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(54) Title: METHOD FOR USING SPUTTERING TARGET AND METHOD FOR MANUFACTURING OXIDE FILM

FIG. 2A

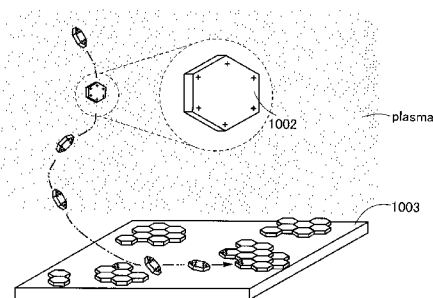
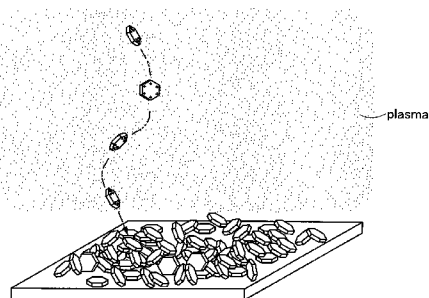


FIG. 2B



(57) Abstract: A method for using a sputtering target which enables an oxide film with a high degree of crystallinity, which contains a plurality of metal elements, to be formed is provided. In the method for using a sputtering target including a polycrystalline oxide containing a plurality of crystal grains which include a cleavage plane, an ion is made to collide with the sputtering target to separate sputtered particles from the cleavage plane, and the sputtered particles are positively charged, so that the sputtered particles are deposited uniformly on a deposition surface while repelling each other.